

FEATURES

Complementary Type The NPN Transistor
 MMBT3904 is Recommended
 Epitaxial Planar Die Construction



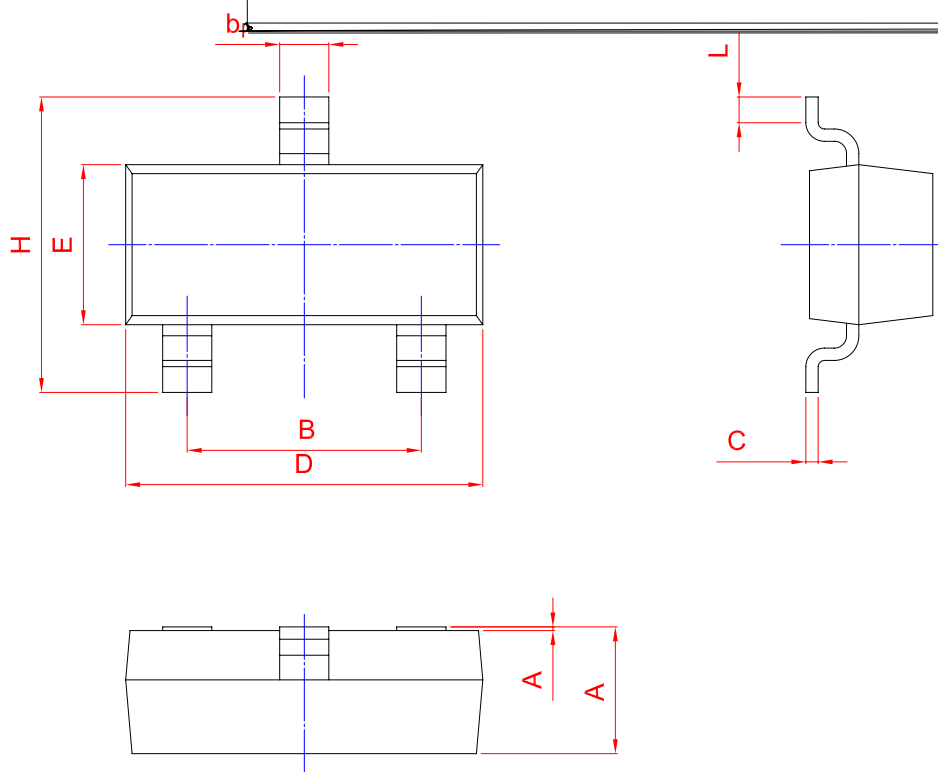
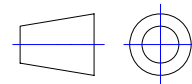
MARKING: 2A

MAXIMUM RATINGS (T_a=25 unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-200	mA
P _C	Total Device Dissipation	200	mW
R _{JA}	Thermal Resistance Junction to Ambient	625	/W
T _J	Junction Temperature	150	
T _{stg}	Storage Temperature	-55 ~ +150	

ELECTRICAL CHARACTERISTICS (T_a=25 unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40		V



UNIT	A		b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95		0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20